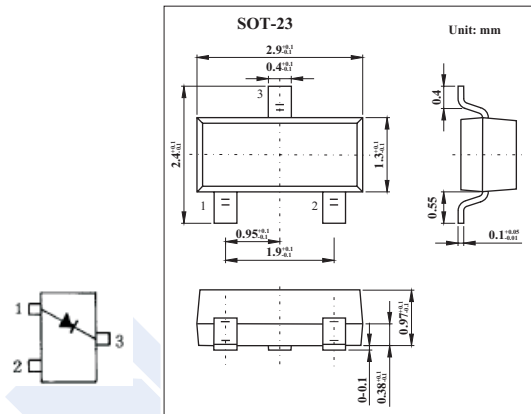


## Silicon Epitaxial Planar Type

### 1SS307

#### ■ Features

- Low forward voltage :  $V_F = 1.0$  V(Typ)
- Low reverse Current :  $I_R = 0.1$  nA (Typ)
- Small total capacitance :  $C_T = 3.0$  pF(Typ)



#### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Maximum (peak) reverse voltage	$V_{RM}$	35	V
Reverse voltage	$V_R$	30	V
Average forward current	$I_O$	100	mA
Maximum (peak) forward current	$I_{FM}$	300	mA
Surge current (10 ms)	$I_{FSM}$	2	A
Power dissipation	$P$	150	mW
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 + 125	$^\circ\text{C}$

#### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	$V_F$	$I_F = 100$ mA		1.0	1.3	V
Reverse current	$I_R$	$V_R = 30$ V		0.1	10	nA
Total capacitance	$C_T$	$V_R = 0, f = 1.0$ MHz		3.0	6.0	pF

#### ■ Marking

Marking	C9
---------	----